

1. Material Substrate GaAlAs (P Type) Removed
Epitaxial Layer GaAlAs (N/P Type)

2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

| Parameter | Symbol | Min | Typ | Max | Unit | Condition |
|-----------------|-----------------|-----|-----|-----|------|------------------------------------|
| Forward Voltage | $V_{F(1)}$ | | 1.1 | | V | IF=10uA |
| | $V_{F(2)}$ | | 1.8 | 2 | V | IF=100mA |
| Reverse Voltage | V_R | 5 | | | V | IR=10uA |
| Power | P_O | 10 | 12 | | mW | IF=100mA |
| Wavelength | λ_P | | 888 | | nm | IF=50mA |
| | $\Delta\lambda$ | | 45 | | nm | IF=50mA |
| Rise Time | T_r | | 25 | | ns | Tp=400ns, Duty=50%, IFP=50mA |
| Fall Time | T_f | | 20 | | ns | |

※ Note : Power is measured by Sorter E/T system with bare chip.

4. Mechanical Data (a) Emission Area ----- 12.8mil x 12.8mil
 (b) Bottom Area ----- 13.8mil x 13.8mil
 (c) Bonding Pad ----- 130um
 (d) Chip Thickness ----- 7mil
 (e) Junction Height ----- 4.6mil

